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Details

Product Status	Active
Number of LABs/CLBs	625
Number of Logic Elements/Cells	5000
Total RAM Bits	169984
Number of I/O	146
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-5e-5qn208i

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Introduction

LatticeXP2 devices combine a Look-up Table (LUT) based FPGA fabric with non-volatile Flash cells in an architecture referred to as flexiFLASH.

The flexiFLASH approach provides benefits including instant-on, infinite reconfigurability, on chip storage with FlashBAK embedded block memory and Serial TAG memory and design security. The parts also support Live Update technology with TransFR, 128-bit AES Encryption and Dual-boot technologies.

The LatticeXP2 FPGA fabric was optimized for the new technology from the outset with high performance and low cost in mind. LatticeXP2 devices include LUT-based logic, distributed and embedded memory, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support and enhanced sysDSP blocks.

Lattice Diamond[®] design software allows large and complex designs to be efficiently implemented using the LatticeXP2 family of FPGA devices. Synthesis library support for LatticeXP2 is available for popular logic synthesis tools. The Diamond software uses the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the LatticeXP2 device. The Diamond tool extracts the timing from the routing and back-annotates it into the design for timing verification.

Lattice provides many pre-designed Intellectual Property (IP) LatticeCORE[™] modules for the LatticeXP2 family. By using these IPs as standardized blocks, designers are free to concentrate on the unique aspects of their design, increasing their productivity.



Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as LUT4s. A LUT4 has 16 possible input combinations. Fourinput logic functions are generated by programming the LUT4. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger LUTs such as LUT6, LUT7 and LUT8, can be constructed by concatenating two or more slices. Note that a LUT8 requires more than four slices.

Ripple Mode

Ripple mode allows efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with async clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Two carry signals, FCI and FCO, are generated per slice in this mode, allowing fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed Single Port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 2 as a 16x1-bit memory. Slice 1 is used to provide memory address and control signals. A 16x2-bit Pseudo Dual Port RAM (PDPR) memory is created by using one slice as the read-write port and the other companion slice as the read-only port.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information on using RAM in LatticeXP2 devices, please see TN1137, <u>LatticeXP2 Memory Usage Guide</u>.

Table 2-3. Number of Slices Required For Implementing Distributed RAM

Number of slices	3 3	

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in the ROM mode. Preloading is accomplished through the programming interface during PFU configuration.



Figure 2-5. Clock Divider Connections



Clock Distribution Network

LatticeXP2 devices have eight quadrant-based primary clocks and between six and eight flexible region-based secondary clocks/control signals. Two high performance edge clocks are available on each edge of the device to support high speed interfaces. The clock inputs are selected from external I/Os, the sysCLOCK PLLs, or routing. Clock inputs are fed throughout the chip via the primary, secondary and edge clock networks.

Primary Clock Sources

LatticeXP2 devices derive primary clocks from four sources: PLL outputs, CLKDIV outputs, dedicated clock inputs and routing. LatticeXP2 devices have two to four sysCLOCK PLLs, located in the four corners of the device. There are eight dedicated clock inputs, two on each side of the device. Figure 2-6 shows the primary clock sources.



Secondary Clock/Control Sources

LatticeXP2 devices derive secondary clocks (SC0 through SC7) from eight dedicated clock input pads and the rest from routing. Figure 2-7 shows the secondary clock sources.

Figure 2-7. Secondary Clock Sources





sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

FlashBAK EBR Content Storage

All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.



MAC sysDSP Element

In this case, the two operands, A and B, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers but the output register is always enabled. The output register is used to store the accumulated value. The Accumulators in the DSP blocks in LatticeXP2 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-21 shows the MAC sysDSP element.

Figure 2-21. MAC sysDSP





register. Similarly, CE and RST are selected from their four respective sources (CE0, CE1, CE2, CE3 and RST0, RST1, RST2, RST3) at each input register, pipeline register and output register.

Signed and Unsigned with Different Widths

The DSP block supports other widths, in addition to x9, x18 and x36 widths, of signed and unsigned multipliers. For unsigned operands, unused upper data bits should be filled to create a valid x9, x18 or x36 operand. For signed two's complement operands, sign extension of the most significant bit should be performed until x9, x18 or x36 width is reached. Table 2-7 provides an example of this.

Table 2-7. Sign Extension Example

Number	Unsigned	Unsigned 9-bit	Unsigned 18-bit	Signed	Two's Complement Signed 9 Bits	Two's Complement Signed 18 Bits
+5	0101	000000101	00000000000000101	0101	00000101	00000000000000101
-6	N/A	N/A	N/A	1010	111111010	1111111111111111010

OVERFLOW Flag from MAC

The sysDSP block provides an overflow output to indicate that the accumulator has overflowed. "Roll-over" occurs and an overflow signal is indicated when any of the following is true: two unsigned numbers are added and the result is a smaller number than the accumulator, two positive numbers are added with a negative sum or two negative numbers are added with a positive sum. Note that when overflow occurs the overflow flag is present for only one cycle. By counting these overflow pulses in FPGA logic, larger accumulators can be constructed. The conditions for the overflow signal for signed and unsigned operands are listed in Figure 2-24.

Figure 2-24. Accumulator Overflow/Underflow





Table 2-11. PIO Signal List

Name	Туре	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK ²	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0 ¹ , QPOS1 ¹	Input to the core	Gearbox pipelined inputs to the core
QNEG0 ¹ , QNEG1 ¹	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.

2. Selected I/O.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

Input Register Block

The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.



Figure 2-31. DQS Local Bus



*DQSXFERDEL shifts ECLK1 by 90% and is not associated with a particular PIO.

Polarity Control Logic

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeXP2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This changes the edge on which the data is registered in the synchronizing registers in the input register block and requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects this transition. This signal is used to control the polarity of the clock to the synchronizing registers.



original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, <u>LatticeXP2 Dual Boot Feature</u>.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

- 1. Device powers up with the default CCLK frequency.
- 2. During configuration, users select a different CCLK frequency.
- 3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, <u>LatticeXP2 sysCON-FIG Usage Guide</u>.

Table 2-14. Selectable	CCLKs and Oscillato	r Freauencies Durina	Configuration and	User Mode

CCLK/Oscillator (MHz)					
2.5 ¹					
3.1 ²					
4.3					
5.4					
6.9					
8.1					
9.2					
10					
13					
15					
20					
26					
32					
40					
54					
80 ³					
163 ³					
1 Software default oscillator frequency					

1. Software default oscillator frequency.

2. Software default CCLK frequency.

3. Frequency not valid for CCLK.



sysIO Single-Ended DC Electrical Characteristics

Input/Output		V _{IL}	VII	1	V _{OL}	V _{OH}					
Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)	l _{OL} 1 (mA)	l _{OH} ¹ (mA)			
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4			
					0.2	V _{CCIO} - 0.2	0.1	-0.1			
LVTTL33	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4			
					0.2	V _{CCIO} - 0.2	0.1	-0.1			
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4			
					0.2	V _{CCIO} - 0.2	0.1	-0.1			
LVCMOS18	-0.3	0.35 V _{CCIO}	0.65 V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	16, 12, 8, 4	-16, -12, -8, -4			
					0.2	V _{CCIO} - 0.2	0.1	-0.1			
LVCMOS15	-0.3	-0.3 0.35 V _{CCIO}	0.65 V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	8, 4	-8, -4			
					0.2	V _{CCIO} - 0.2	0.1	-0.1			
	-0.3	0.35 V	0.65 V	3.6	0.4	V _{CCIO} - 0.4	6, 2	-6, -2			
LVCIVIOS12 -0.	-0.5	0.35 V _{CC}	0.05 V _{CC}	5.0	0.2	V _{CCIO} - 0.2	0.1	-0.1			
PCI33	-0.3	0.3 V _{CCIO}	0.5 V _{CCIO}	3.6	0.1 V _{CCIO}	0.9 V _{CCIO}	1.5	-0.5			
SSTL33_I	-0.3	V _{REF} - 0.2	V _{REF} + 0.2	3.6	0.7	V _{CCIO} - 1.1	8	-8			
SSTL33_II	-0.3	V _{REF} - 0.2	V _{REF} + 0.2	3.6	0.5	V _{CCIO} - 0.9	16	-16			
SSTI 25 I	-0.3	-0.3	-0.3	-0.3	Vpcc - 0 18	Vp== ± 0.18	3.6	0.54	Vacua - 0.62	7.6	-7.6
001220_1	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.04	ACCIO - 0.05	12	-12			
SSTI 25 II	-0.3	V0 18	V+0 18	36	0.35	Vac: a 0.43	15.2	-15.2			
001225_11	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.00	ACCIO - 0.42	20	-20			
SSTL18_I	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	3.6	0.4	V _{CCIO} - 0.4	6.7	-6.7			
	-0.3	V 0 125	V ± 0 125	36	0.28	Vac 0.28	8	-8			
001210_1	-0.0	V _{REF} - 0.125	v _{REF} + 0.125	3.0	0.20	V _{CCIO} - 0.28	11	-11			
HSTI 15 I	-0.3	Vpcc - 0 1		3.6	0.4		4	-4			
	0.0	.5 V _{REF} - 0.1	*REF + 0.1	3.0	0.4	VCCIO - 0.4	8	-8			
HSTI 18 I	-0.3	Vp== - 0 1	V . 0.1	26	0.4		8	-8			
	0.0	KEF - 0.1		0.0	U.T		12	-12			
HSTL18_II	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	3.6	0.4	V _{CCIO} - 0.4	16	-16			

Over Recommended Operating Conditions

 The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O bank and the end of an I/O bank, as shown in the logic signal connections table shall not exceed n * 8mA, where n is the number of I/Os between bank GND connections or between the last GND in a bank and the end of a bank.



MLVDS

The LatticeXP2 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.





Table 3-5. MLVDS DC Conditions¹

		Тур		
Parameter	Description	Ζο=50 Ω	Ζο=70 Ω	Units
V _{CCIO}	Output Driver Supply (+/-5%)	2.50	2.50	V
Z _{OUT}	Driver Impedance	10.00	10.00	Ω
R _S	Driver Series Resistor (+/-1%)	35.00	35.00	Ω
R _{TL}	Driver Parallel Resistor (+/-1%)	50.00	70.00	Ω
R _{TR}	Receiver Termination (+/-1%)	50.00	70.00	Ω
V _{OH}	Output High Voltage (After R _{TL})	1.52	1.60	V
V _{OL}	Output Low Voltage (After R _{TL})	0.98	0.90	V
V _{OD}	Output Differential Voltage (After R _{TL})	0.54	0.70	V
V _{CM}	Output Common Mode Voltage	1.25	1.25	V
I _{DC}	DC Output Current	21.74	20.00	mA

1. For input buffer, see LVDS table.

For further information on LVPECL, RSDS, MLVDS, BLVDS and other differential interfaces please see details of additional technical information at the end of this data sheet.



Typical Building Block Function Performance¹

Pin-to-Pin Performance (LVCMOS25 12mA Drive)

Function	-7 Timing	Units
Basic Functions		
16-bit Decoder	4.4	ns
32-bit Decoder	5.2	ns
64-bit Decoder	5.6	ns
4:1 MUX	3.7	ns
8:1 MUX	3.9	ns
16:1 MUX	4.3	ns
32:1 MUX	4.5	ns

Register-to-Register Performance

Function	-7 Timing	Units
Basic Functions		
16-bit Decoder	521	MHz
32-bit Decoder	537	MHz
64-bit Decoder	484	MHz
4:1 MUX	744	MHz
8:1 MUX	678	MHz
16:1 MUX	616	MHz
32:1 MUX	529	MHz
8-bit Adder	570	MHz
16-bit Adder	507	MHz
64-bit Adder	293	MHz
16-bit Counter	541	MHz
32-bit Counter	440	MHz
64-bit Counter	321	MHz
64-bit Accumulator	261	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	315	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	315	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	231	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	760	MHz
32x2 Pseudo-Dual Port RAM	455	MHz
64x1 Pseudo-Dual Port RAM	351	MHz
DSP Functions		
18x18 Multiplier (All Registers)	342	MHz
9x9 Multiplier (All Registers)	342	MHz
36x36 Multiply (All Registers)	330	MHz
18x18 Multiply/Accumulate (Input and Output Registers)	218	MHz
18x18 Multiply-Add/Sub-Sum (All Registers)	292	MHz



EBR Timing Diagrams





Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

Figure 3-7. Read/Write Mode with Input and Output Registers





Flash Download Time (from On-Chip Flash to SRAM)

Over Recommended Operating Conditions

Symbol	Parar	neter	Min.	Тур.	Max.	Units
	PBOGBAMN Low-to-	XP2-5	—	1.8	2.1	ms
		XP2-8	—	1.9	2.3	ms
	High. Transition to Done	XP2-17	—	1.7	2.0	ms
t _{REFRESH}	High.	XP2-30	—	2.0	2.1	ms
		XP2-40	—	2.0	2.3	ms
	Power-up refresh when PROGRAMN is pulled	XP2-5	—	1.8	2.1	ms
		XP2-8	—	1.9	2.3	ms
		XP2-17	—	1.7	2.0	ms
	$(V_{CC}=V_{CC} Min)$	XP2-30	—	2.0	2.1	ms
		XP2-40		2.0	2.3	ms

Flash Program Time

Over Recommended Operating Conditions

	Flash Density		Program Time	
Device			Тур.	Units
	1.0M	TAG	1.0	ms
XF2-5	1.2101	Main Array	1.1	S
XP2-8 2.0M	2.0M	TAG	1.0	ms
	2.0101	Main Array	1.4	S
XP2-17	3.6M	TAG	1.0	ms
		Main Array	1.8	S
	6.014	TAG	2.0	ms
XP2-30	0.0101	Main Array	3.0	S
XP2-40	8 OM	TAG	2.0	ms
	0.000	Main Array	4.0	S

Flash Erase Time

Over Recommended Operating Conditions

	Flash Density		Erase Time	
Device			Тур.	Units
YP2_5	1.2M	TAG	1.0	s
XI 2-3	1.2101	Main Array	3.0	s
XP2-8	2.0M	TAG	1.0	S
	2.0101	Main Array	4.0	s
XP2-17	3.6M	TAG	1.0	s
		Main Array	5.0	S
XP2-30 6	6.0M	TAG	2.0	s
		Main Array	7.0	s
XP2-40	8.0M	TAG	2.0	S
	0.00	Main Array	9.0	S



Switching Test Conditions

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

 Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	R ₂	CL	Timing Ref.	V _T
		8		LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞		0pF	LVCMOS 1.8 = V _{CCIO} /2	
				LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V _{CCIO} /2	_
LVCMOS 2.5 I/O (Z -> H)	8	1MΩ		V _{CCIO} /2	
LVCMOS 2.5 I/O (Z -> L)	1MΩ	∞		V _{CCIO} /2	V _{CCIO}
LVCMOS 2.5 I/O (H -> Z)	8	100		V _{OH} - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	∞		V _{OL} + 0.10	V _{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.



LatticeXP2 Family Data Sheet Ordering Information

February 2012

Data Sheet DS1009

Part Number Description



Ordering Information

The LatticeXP2 devices are marked with a single temperature grade, either Commercial or Industrial, as shown below.



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Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	30
LFXP2-30E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	30
LFXP2-30E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	30
LFXP2-30E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	30
LFXP2-30E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	30
LFXP2-30E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	30
LFXP2-30E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	30
LFXP2-30E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	30
LFXP2-30E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	40
LFXP2-40E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	40
LFXP2-40E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	40
LFXP2-40E-5FN672C	1.2V	-5	Lead-Free fpBGA	672	COM	40
LFXP2-40E-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	40
LFXP2-40E-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	40

Industrial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	5
LFXP2-5E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	5
LFXP2-5E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	5
LFXP2-5E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	5
LFXP2-5E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	5
LFXP2-5E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	5
LFXP2-5E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	5
LFXP2-5E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132I	1.2V	-5	Lead-Free csBGA	132	IND	8
LFXP2-8E-6MN132I	1.2V	-6	Lead-Free csBGA	132	IND	8
LFXP2-8E-5TN144I	1.2V	-5	Lead-Free TQFP	144	IND	8
LFXP2-8E-6TN144I	1.2V	-6	Lead-Free TQFP	144	IND	8
LFXP2-8E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	8
LFXP2-8E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	8
LFXP2-8E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	8
LFXP2-8E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	8



Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5F484I	1.2V	-5	fpBGA	484	IND	40
LFXP2-40E-6F484I	1.2V	-6	fpBGA	484	IND	40
LFXP2-40E-5F672I	1.2V	-5	fpBGA	672	IND	40
LFXP2-40E-6F672I	1.2V	-6	fpBGA	672	IND	40



Date	Version	Section	Change Summary
April 2008	01.4	DC and Switching	Updated Flash Download Time (From On-Chip Flash to SRAM) Table
(cont.)	(cont.)	Characteristics (cont.)	Updated Flash Program Time Table
			Updated Flash Erase Time Table
			Updated FlashBAK (from EBR to Flash) Table
			Updated Hot Socketing Specifications Table footnotes
		Pinout Information	Updated Signal Descriptions Table
June 2008	01.5	Architecture	Removed Read-Before-Write sysMEM EBR mode.
			Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed Read-Before-Write sysMEM EBR mode.
		Pinout Information	Updated DDR Banks Bonding Out per I/O Bank section of Pin Informa- tion Summary Table.
August 2008	01.6	—	Data sheet status changed from preliminary to final.
		Architecture	Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed "8W" specification from Hot Socketing Specifications table.
			Removed "8W" footnote from DC Electrical Characteristics table.
			Updated Register-to-Register Performance table.
		Ordering Information	Removed "8W" option from Part Number Description.
			Removed XP2-17 "8W" OPNs.
April 2011	01.7	DC and Switching Characteristics	Recommended Operating Conditions table, added footnote 5.
			On-Chip Flash Memory Specifications table, added footnote 1.
			BLVDS DC Conditions, corrected column title to be Z0 = 90 ohms.
			sysCONFIG Port Timing Specifications table, added footnote 1 for t _{DINIT} .
January 2012	01.8	Multiple	Added support for Lattice Diamond design software.
		Architecture	Corrected information regarding SED support.
		DC and Switching Characteristics	Added reference to ESD Performance Qualification Summary informa- tion.
May 2013	01.9	All	Updated document with new corporate logo.
		Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			Added information regarding SED support.
		DC and Switching Characteristics	Removed Input Clock Rise/Fall Time 1ns max from the sysCLOCK PLL Timing table.
		Ordering Information	Updated topside mark in Ordering Information diagram.
March 2014	02.0	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Added information on POR signal deactivation.
August 2014	02.1	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Described user I/Os during power up and before FPGA core logic is active.
September 2014	2.2	DC and Switching Characteristics	Updated Switching Test Conditions section. Re-linked missing figure.